OptiMOS™-T Power-Transistor

AEC Qualified

RoHS

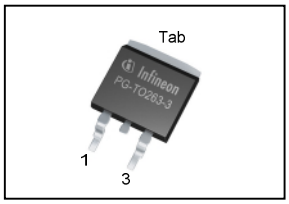
Product Summary

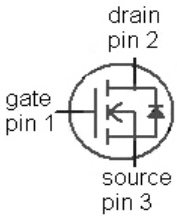
V_{DS}	100	V
$R_{DS(on),max}$	26.3	mΩ
I_D	35	A

Features

- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

PG-TO263-3-2





Type	Package	Marking
IPB35N10S3L-26	PG-TO263-3-2	3N10L26

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25°C, V_{GS}=10V	35	A
		T_C=100°C, V_{GS}=10V[1)]	25	
Pulsed drain current[1)]	$I_{D,pulse}$	T_C=25°C	140	
Avalanche energy, single pulse[1)]	E_{AS}	I_D=17A	175	mJ
Avalanche current, single pulse	I_{AS}	-	35	A
Gate source voltage[2)]	V_{GS}	-	±20	V
Power dissipation	P_{tot}	T_C=25°C	71	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics[1]						
Thermal resistance, junction - case	R_{thJC}		-	-	2.1	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3]	-	-	40	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D= 1mA	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=39µA	1.2	1.7	2.4	
Zero gate voltage drain current	I_{DSS}	V_{DS}=80V, V_{GS}=0V, T_j=25°C	-	0.01	0.1	µA
		V_{DS}=80V, V_{GS}=0V, T_j=125°C[1]	-	1	10	
Gate-source leakage current	I_{GSS}	V_{GS}=20V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=4.5V, I_D=35A	-	24.8	32.2	mΩ
		V_{GS}=10 V, I_D=35 A	-	20.3	26.3	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics[1]						
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	2070	2700	pF
Output capacitance	C_{oss}		-	460	600	
Reverse transfer capacitance	C_{rss}		-	50	75	
Turn-on delay time	$t_{d(on)}$	V_{DD}=20V, V_{GS}=10V, I_D=35A, R_G=3.5Ω	-	6	-	ns
Rise time	t_r		-	4	-	
Turn-off delay time	$t_{d(off)}$		-	18	-	
Fall time	t_f		-	3	-	
Gate Charge Characteristics[1]						
Gate to source charge	Q_{gs}	V_{DD}=80V, I_D=35A, V_{GS}=0 to 10V	-	8	10	nC
Gate to drain charge	Q_{gd}		-	5	8	
Gate charge total	Q_g		-	30	39	
Gate plateau voltage	$V_{plateau}$		-	3.7	-	V
Reverse Diode						
Diode continous forward current[1]	I_S	T_C=25°C	-	-	35	A
Diode pulse current[1]	$I_{S,pulse}$		-	-	140	
Diode forward voltage	V_{SD}	V_{GS}=0V, I_F=35A, T_j=25°C	0.6	1	1.2	V
Reverse recovery time[1]	t_{rr}	V_R=50V, I_F=I_S, di_F/dt=100A/µs	-	79	-	ns
Reverse recovery charge[1]	Q_{rr}		-	150	-	nC

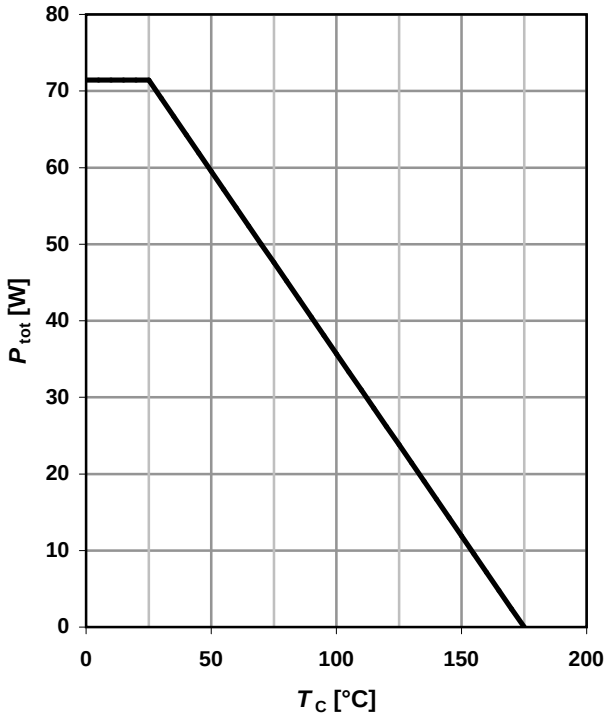
[1] Defined by design. Not subject to production test.

[2] Qualified with V_{GS} = +20/-5V.

[3] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

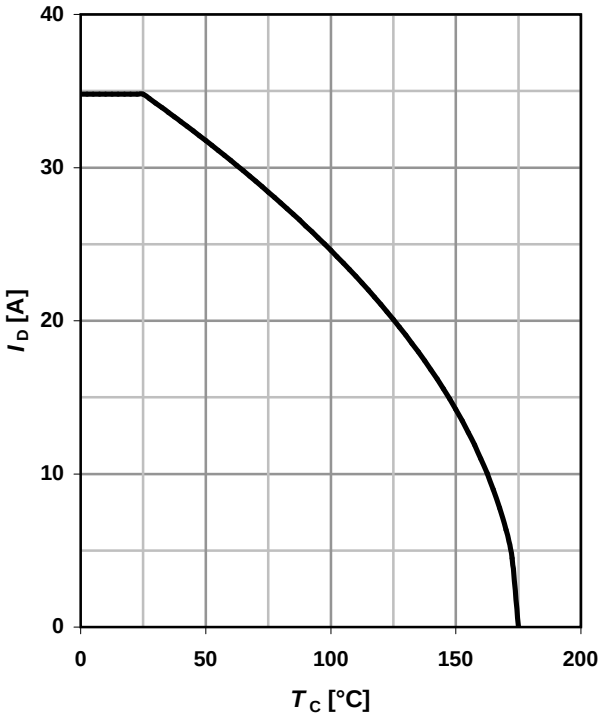
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \geq 6$ V



2 Drain current

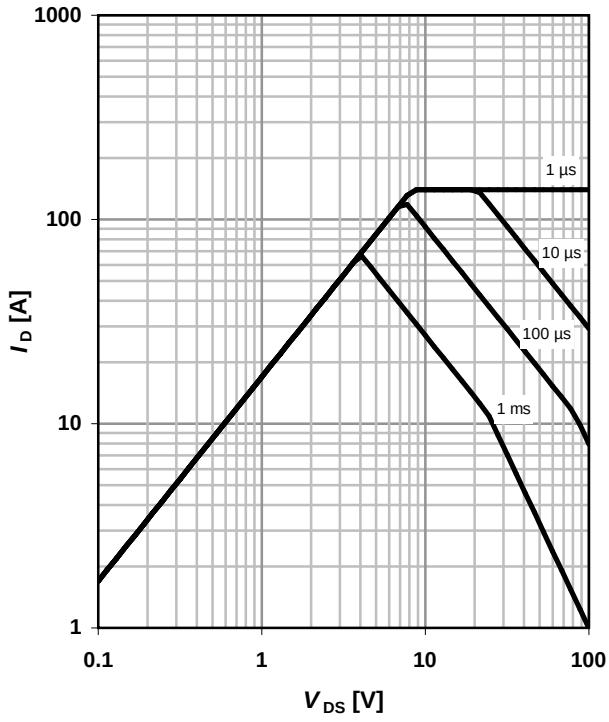
$I_D = f(T_C)$; $V_{GS} \geq 6$ V



3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$

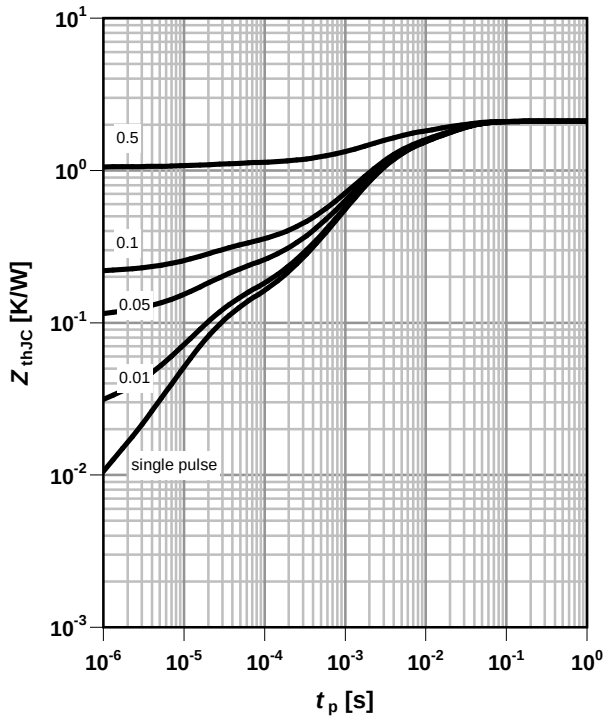
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

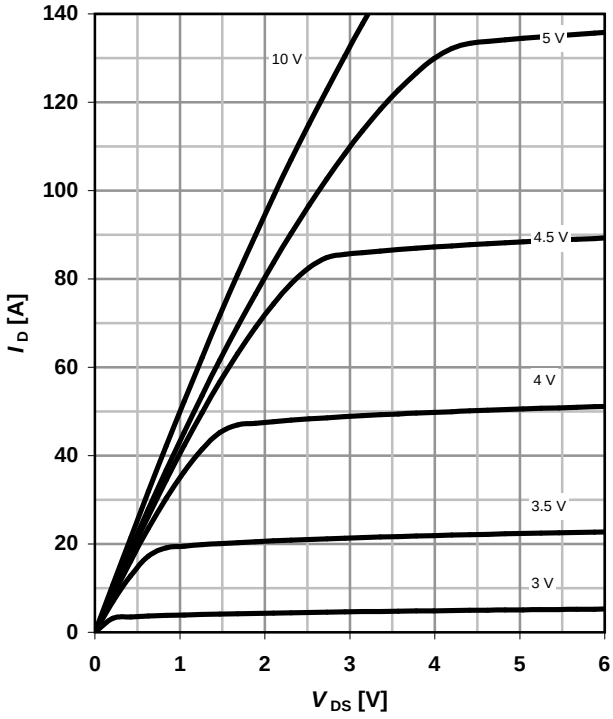
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C

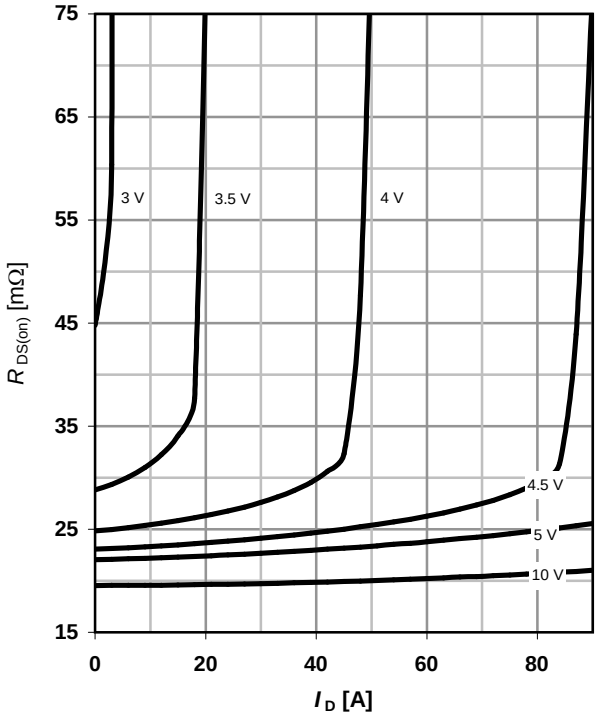
parameter: V_{GS}



6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D)$; $T_j = 25$ °C

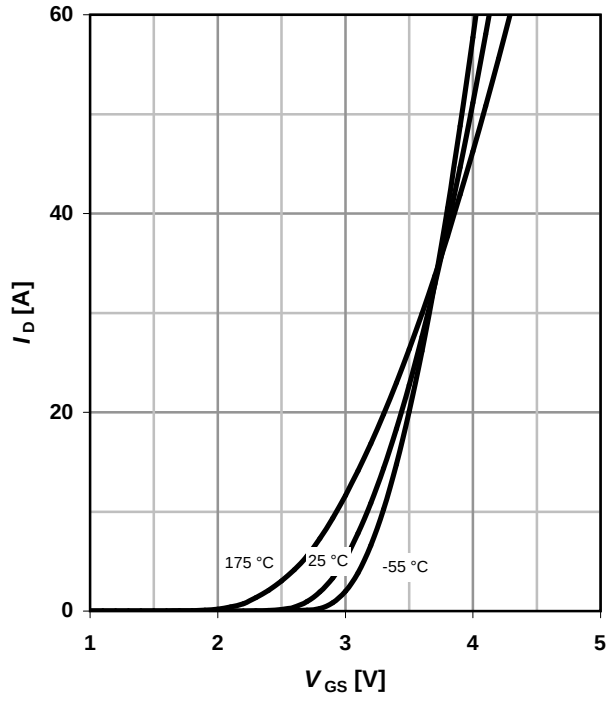
parameter: V_{GS}



7 Typ. transfer characteristics

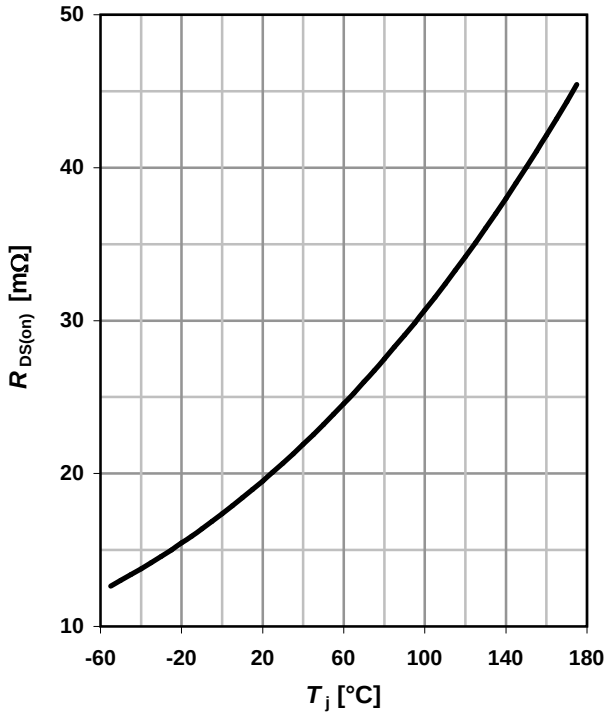
$I_D = f(V_{GS})$; $V_{DS} = 6$V

parameter: T_j



8 Typ. drain-source on-state resistance

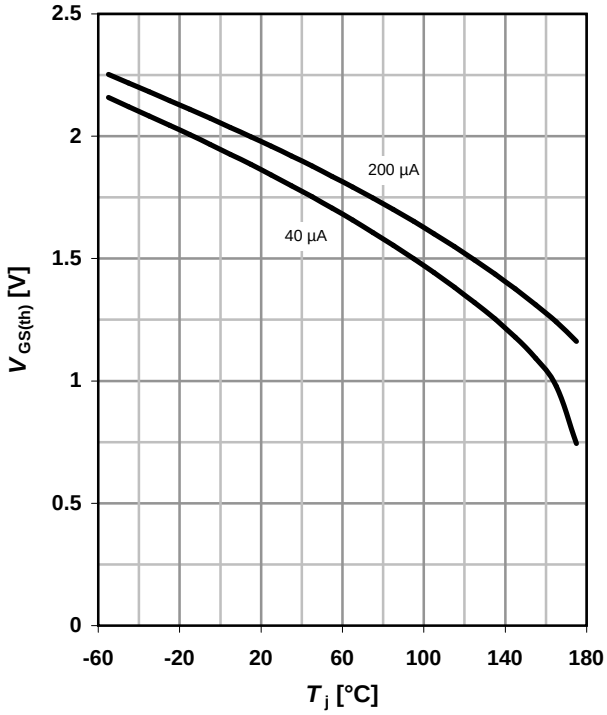
$R_{DS(on)} = f(T_j)$; $I_D = 30$ A; $V_{GS} = 10$ V



9 Typ. gate threshold voltage

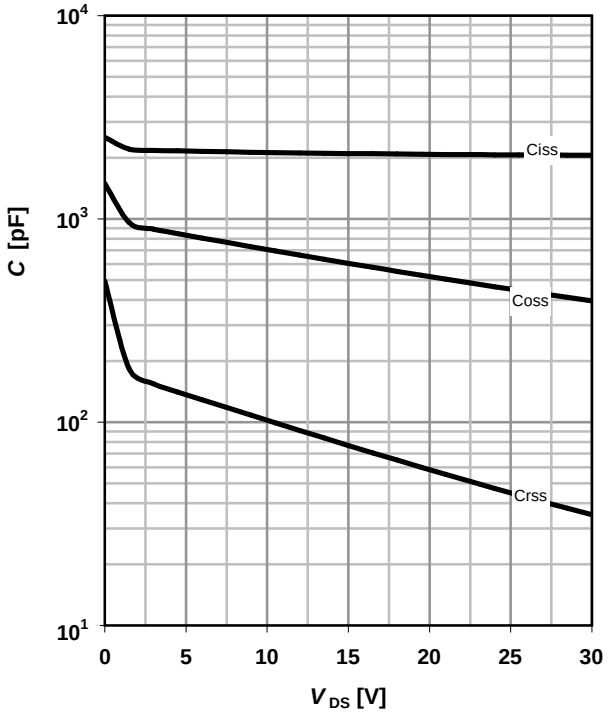
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

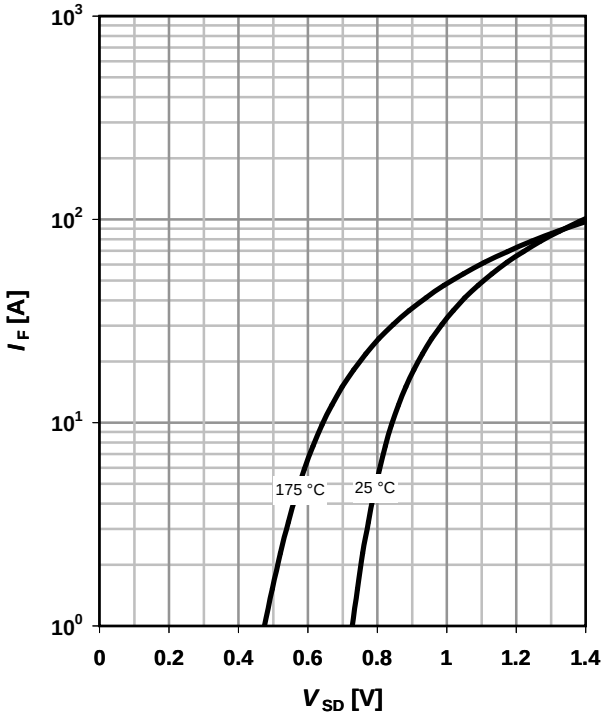
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



11 Typ. forward diode characteristicis

IF = f(V_{SD})

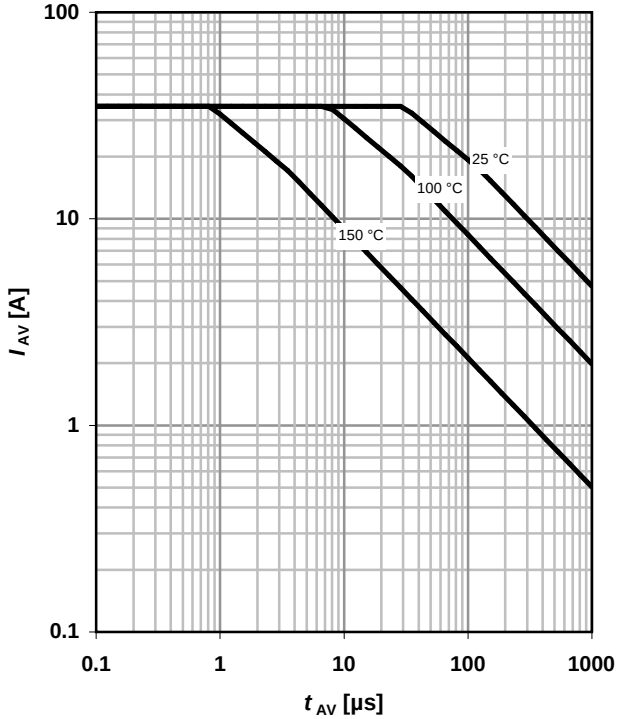
parameter: T_j



12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$

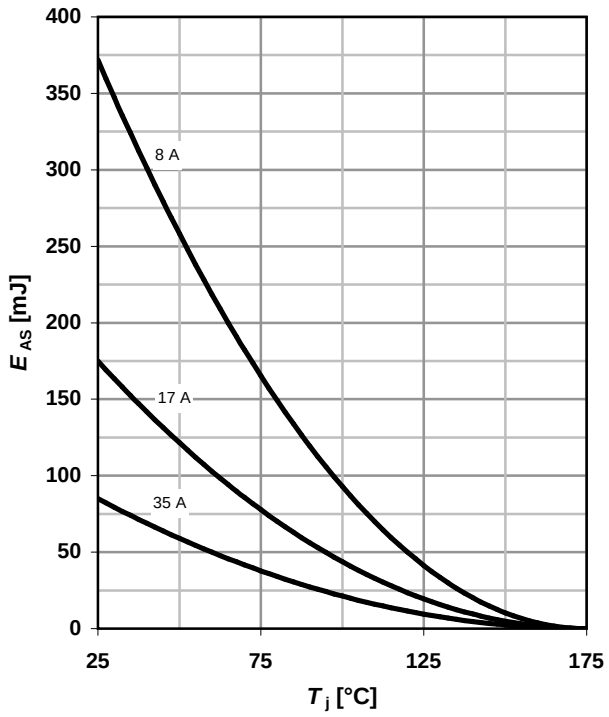
parameter: $T_{j(start)}$



13 Typ. avalanche energy

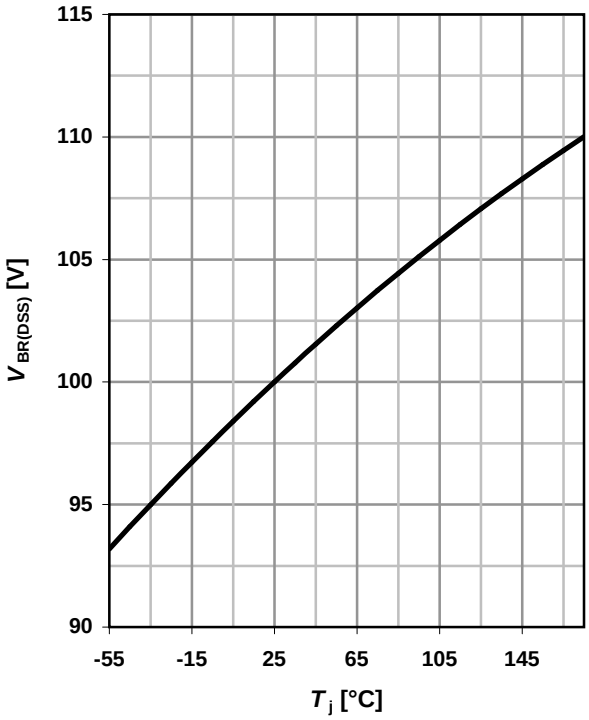
$E_{AS} = f(T_j)$

parameter: I_D



14 Drain-source breakdown voltage

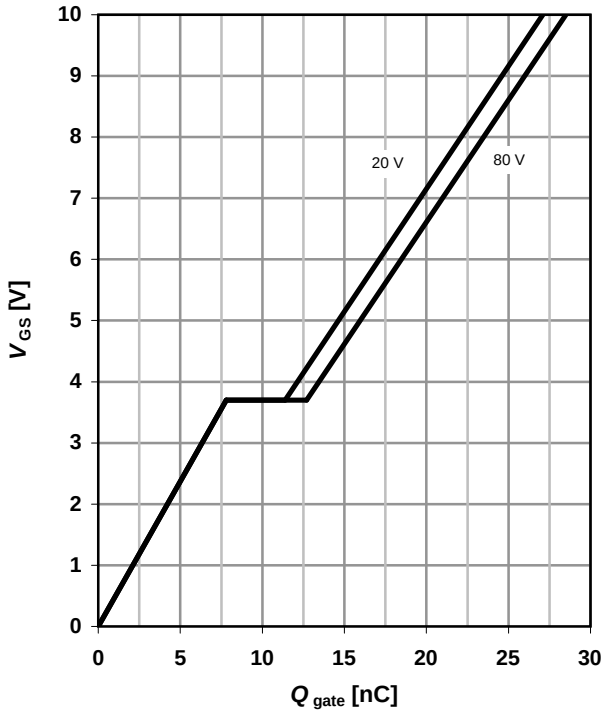
$V_{BR(DSS)} = f(T_j)$; $I_D = 1$ mA



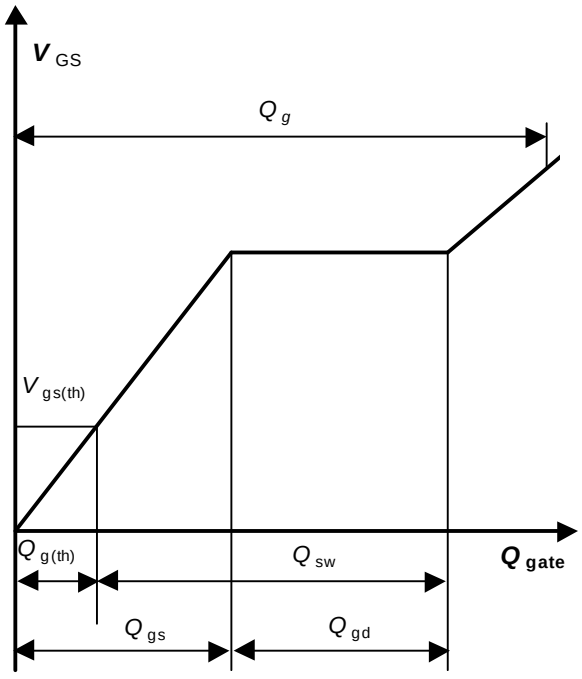
15 Typ. gate charge

$V_{GS} = f(Q_{gate})$; $I_D = 35$ A pulsed

parameter: V_{DD}



16 Gate charge waveforms



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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Rev 1.0	25.02.2010	final data sheet
Rev 1.1	17.05.2011	$I_{D,pulse}$ corrected